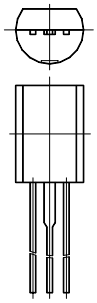
SHENZHEN HAOCHANG SEMICONDUCTOR CO.,LTD.

TO-92L Plastic-Encapsulate Transistors

2SC2236 TRANSISTOR (NPN)

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



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FEATURE

Complementary to 2SA966 and 3 Watts output Applications.

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 1mA , I_E=0	30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 10mA , I_B=0	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=30V , I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V , I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=2 V, I_C= 500mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 1.5 A, I_B= 0.03A			2	V
Base-emitter voltage	V_{BE}	I_C= 500 mA, V_{CE}= 2V			1	V
Transition frequency	f_T	V_{CE}= 2V, I_C= 500mA		120		MHz
Collector output Capacitance	C_{ob}	V_{CB}= 10V, I_E= 0,f=1MHz			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320